"Comparative study of structural properties and photoluminescence in InGaN layers with a high In content". Vantomme A, Wu MF, Hogg S, van Landuyt J, et al, Internet journal of nitride semiconductor research

T2 - Symposium on GaN and Related Alloys Held at the MRS Fall Meeting, NOV 29-DEC 03, 1999, BOSTON, MASSACHUSETTS **5**, art. no.-W11.38 (2000)